

<b>Notice of Allowability</b>	<b>Application No.</b>	<b>Applicant(s)</b>	
	10/808,833	HOTTA, KAZUSHIGE	
	Examiner Tuan Quach	Art Unit 2826	

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address--

All claims being allowable, PROSECUTION ON THE MERITS IS (OR REMAINS) CLOSED in this application. If not included herewith (or previously mailed), a Notice of Allowance (PTOL-85) or other appropriate communication will be mailed in due course. **THIS NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RIGHTS.** This application is subject to withdrawal from issue at the initiative of the Office or upon petition by the applicant. See 37 CFR 1.313 and MPEP 1308.

1.  This communication is responsive to response filed March 17, 2005.

2.  The allowed claim(s) is/are 1-9.

3.  The drawings filed on March 25, 2004 are accepted by the Examiner.

4.  Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).

a)  All    b)  Some\*    c)  None    of the:

1.  Certified copies of the priority documents have been received.

2.  Certified copies of the priority documents have been received in Application No. \_\_\_\_\_.

3.  Copies of the certified copies of the priority documents have been received in this national stage application from the International Bureau (PCT Rule 17.2(a)).

\* Certified copies not received: \_\_\_\_\_.

Applicant has THREE MONTHS FROM THE "MAILING DATE" of this communication to file a reply complying with the requirements noted below. Failure to timely comply will result in ABANDONMENT of this application.

**THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.**

5.  A SUBSTITUTE OATH OR DECLARATION must be submitted. Note the attached EXAMINER'S AMENDMENT or NOTICE OF INFORMAL PATENT APPLICATION (PTO-152) which gives reason(s) why the oath or declaration is deficient.

6.  CORRECTED DRAWINGS ( as "replacement sheets") must be submitted.

(a)  including changes required by the Notice of Draftsperson's Patent Drawing Review ( PTO-948) attached  
1)  hereto or 2)  to Paper No./Mail Date \_\_\_\_\_.

(b)  including changes required by the attached Examiner's Amendment / Comment or in the Office action of  
Paper No./Mail Date \_\_\_\_\_.

Identifying indicia such as the application number (see 37 CFR 1.84(c)) should be written on the drawings in the front (not the back) of each sheet. Replacement sheet(s) should be labeled as such in the header according to 37 CFR 1.121(d).

7.  DEPOSIT OF and/or INFORMATION about the deposit of BIOLOGICAL MATERIAL must be submitted. Note the attached Examiner's comment regarding REQUIREMENT FOR THE DEPOSIT OF BIOLOGICAL MATERIAL.

#### Attachment(s)

- |   |  |
|---|--|
| 1. <input checked="" type="checkbox"/> Notice of References Cited (PTO-892)   | 5. <input type="checkbox"/> Notice of Informal Patent Application (PTO-152)            |
| 2. <input type="checkbox"/> Notice of Draftsperson's Patent Drawing Review (PTO-948)  | 6. <input type="checkbox"/> Interview Summary (PTO-413),<br>Paper No./Mail Date _____. |
| 3. <input checked="" type="checkbox"/> Information Disclosure Statements (PTO-1449 or PTO/SB/08),<br>Paper No./Mail Date <u>3/25/04</u> | 7. <input type="checkbox"/> Examiner's Amendment/Comment                               |
| 4. <input type="checkbox"/> Examiner's Comment Regarding Requirement for Deposit<br>of Biological Material                              | 8. <input checked="" type="checkbox"/> Examiner's Statement of Reasons for Allowance   |
|   | 9. <input type="checkbox"/> Other _____.   |

Tuan Quach  
Primary Examiner

## REASONS FOR ALLOWANCE

The following is an examiner's statement of reasons for allowance:

Claims 1-9 are allowed. The prior art singly or in combination does not teach or suggest the claimed invention in claim 1 regarding a first thin film transistor that is formed on the transparent insulating substrate, a second thin film transistor that is formed on the transparent insulating substrate, the second thin film transistor having a characteristic that differs from a characteristic of the first thin film transistor wherein an active layer of the first thin film transistor has a thickness greater than or equal to 50 nm, and an average crystal grain diameter greater than or equal to 1  $\mu\text{m}$  and an active layer of the second thin film transistor has a thickness less than or equal to 60 nm and a average crystal grain diameter of less than 1  $\mu\text{m}$ , taken in the context of the remaining limitations of claim 1. The prior art also does not teach or suggest the claimed invention in claim 6 regarding a first thin film transistor that is formed on a transparent insulating substrate, and a second thin film transistor that is formed on the transparent insulating substrate, the second thin film transistor having a characteristic that differs from a characteristic of the first thin film transistor, wherein an active layer of the first thin film transistor has an average crystal grain diameter greater than or equal to 1  $\mu\text{m}$  and an active layer of the second thin film transistor has an average crystal grain diameter less than 1  $\mu\text{m}$  and a gate insulating film of the first thin film transistor is arranged to be thinner than a gate insulating film of the second thin film transistor, taken in the context

of the remaining limitations of claim 6. Claims 2-5 and 7-9 are allowed as they depend from claims 1 and 6, respectively and include all the limitations therein.

The prior art made of record and not relied upon is considered pertinent to applicant's disclosure. Takayama et al. (5,677,549), Zhang et al. (5,811,328), Yamazaki et al. (6,498,369), Yoshiyama et al. (6,541,823), Tai et al. (2004/0257486) are made of record together with JP- 11-284188 and 6-125084 cited by applicant. The prior art does not teach or suggest the claimed inventions as delineated above.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Any inquiry concerning this communication or earlier communications from the examiner should be directed to examiner Quach whose telephone number is (571) 272-1717. The examiner can normally be reached on M - F from 8:30 AM to 4:30 PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor Nathan Flynn can be reached on (571) 272-1915. The fax phone number for the organization where this application or proceeding is assigned is (703) 872-9306.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (571) 272-1562.



Tuan Quach  
Primary Examiner